6 Lake Street, Lawrence, MA 01841
1-800-446-1158 / (978) 620-2600 / Fax: (978) 689-0803
Website: http: //www.microsemi.com

## NPN POWER SILICON TRANSISTOR <br> Qualified per MIL-PRF-19500/534

## DEVICES

2N5002 2N5004

LEVELS
JAN
JANTX
JANTXV JANS

ABSOLUTE MAXIMUM RATINGS ( $T_{C}=+25^{\circ} \mathrm{C}$ unless otherwise noted)

| Parameters / Test Conditions | Symbol | Value | Unit |
| :---: | :---: | :---: | :---: |
| Collector-Emitter Voltage | $\mathrm{V}_{\text {CEO }}$ | 80 | V |
| Collector-Base Voltage | $\mathrm{V}_{\text {CBo }}$ | 100 | V |
| Emitter-Base Voltage | $\mathrm{V}_{\text {Ebo }}$ | 5.5 | V |
| Collector Current | $\begin{aligned} & \hline \mathrm{I}_{\mathrm{C}}{ }^{(3)} \\ & \mathrm{I}_{\mathrm{C}}{ }^{3} \\ & \hline \end{aligned}$ | $\begin{gathered} \hline 5.0 \\ 10 \end{gathered}$ | A |
| $\begin{array}{ll}\text { Total Power Dissipation } & \text { @ } \mathrm{T}_{\mathrm{A}}=+25^{\circ} \mathrm{C}^{(1)} \\ & @ \mathrm{~T}_{\mathrm{C}}=+25^{\circ} \mathrm{C}^{(2)}\end{array}$ | $\mathrm{P}_{\mathrm{T}}$ | $\begin{aligned} & 2.0 \\ & 58 \\ & \hline \end{aligned}$ | W |
| Operating \& Storage Junction Temperature Range | $\mathrm{T}_{\mathrm{J}}, \mathrm{T}_{\text {stg }}$ | -65 to +200 | ${ }^{\circ} \mathrm{C}$ |
| Thermal Resistance, Junction-to Case | $\mathrm{R}_{\text {өJC }}$ | 3.0 | ${ }^{\circ} \mathrm{C} / \mathrm{W}$ |
| Thermal Resistance, Junction-to Ambient | $\mathrm{R}_{\text {日JA }}$ | 88 | ${ }^{\circ} \mathrm{C} / \mathrm{W}$ |

Note:

1) Derate linearly $11.4 \mathrm{~mW} /{ }^{\circ} \mathrm{C}$ for $\mathrm{T}_{\mathrm{A}}>+25^{\circ} \mathrm{C}$
2) Derate linearly $331 \mathrm{~mW} /{ }^{\circ} \mathrm{C}$ for $\mathrm{T}_{\mathrm{C}}>+25^{\circ} \mathrm{C}$
3) This value applies for $\mathrm{P}_{\mathrm{W}} \leq 8.3 \mathrm{~ms}$, duty cycle $\leq 1 \%$

ELECTRICAL CHARACTERISTICS $\left(T_{A}=+25^{\circ} \mathrm{C}\right.$, unless otherwise noted)

| Parameters / Test Conditions | Symbol | Min. | Max. | Unit |
| :---: | :---: | :---: | :---: | :---: |
| OFF CHARACTERISTICS |  |  |  |  |
| Collector-Emitter Breakdown Voltage $\mathrm{I}_{\mathrm{C}}=100 \mathrm{mAdc}$ | $\mathrm{V}_{\text {(BR)CEO }}$ | 80 |  | Vdc |
| Collector-Emitter Cutoff Current $\mathrm{V}_{\mathrm{CE}}=40 \mathrm{Vdc}, \mathrm{I}_{\mathrm{B}}=0$ | $\mathrm{I}_{\text {CEO }}$ |  | 50 | $\mu \mathrm{Adc}$ |
| Collector-Emitter Cutoff Current <br> $\mathrm{V}_{\mathrm{CE}}=60 \mathrm{Vdc}, \mathrm{V}_{\mathrm{BE}}=0 \mathrm{Vdc}$ <br> $\mathrm{V}_{\mathrm{CE}}=100 \mathrm{Vdc}, \mathrm{V}_{\mathrm{BE}}=0 \mathrm{Vdc}$ | $\mathrm{I}_{\text {CES }}$ |  | $\begin{aligned} & 1.0 \\ & 1.0 \end{aligned}$ | $\mu \mathrm{Adc}$ <br> mAdc |
| Emitter-Base Cutoff Current $\begin{aligned} & \mathrm{V}_{\mathrm{BE}}=4.0 \mathrm{Vdc}, \mathrm{I}_{\mathrm{C}}=0 \\ & \mathrm{~V}_{\mathrm{BE}}=5.5 \mathrm{Vdc}, \mathrm{I}_{\mathrm{C}}=0 \end{aligned}$ | $\mathrm{I}_{\text {EbO }}$ |  | $\begin{aligned} & 1.0 \\ & 1.0 \end{aligned}$ | mAdc |



TO-59

6 Lake Street, Lawrence, MA 01841
1-800-446-1158 / (978) 620-2600 / Fax: (978) 689-0803
Website: http: //www.microsemi.com

## NPN POWER SILICON TRANSISTOR <br> Qualified per MIL-PRF-19500/534

## DYNAMIC CHARACTERISTICS

| Parameters / Test Conditions |  | Symbol | Min. | Max. | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: |
| Forward-Current Transfer Ratio |  |  |  |  |  |
| $\mathrm{I}_{\mathrm{C}}=50 \mathrm{mAdc}, \mathrm{V}_{\mathrm{CE}}=5.0 \mathrm{Vdc}$ | 2N5002 | $\mathrm{h}_{\text {FE }}$ | 20 | --- |  |
| $\mathrm{I}_{\mathrm{C}}=2.5 \mathrm{Adc}, \mathrm{V}_{\mathrm{CE}}=5.0 \mathrm{Vdc}$ |  |  | 30 | 90 |  |
| $\mathrm{I}_{\mathrm{C}}=5.0 \mathrm{Adc}, \mathrm{V}_{\mathrm{CE}}=5.0 \mathrm{Vdc}$ |  |  | 20 | --- |  |
| $\mathrm{I}_{\mathrm{C}}=50 \mathrm{mAdc}, \mathrm{V}_{\mathrm{CE}}=5.0 \mathrm{Vdc}$ | 2N5004 |  | 50 | --- |  |
| $\mathrm{I}_{\mathrm{C}}=2.5 \mathrm{Adc}, \mathrm{V}_{\mathrm{CE}}=5.0 \mathrm{Vdc}$ |  |  | 70 | 200 |  |
| $\mathrm{I}_{\mathrm{C}}=5.0 \mathrm{Adc}, \mathrm{V}_{\mathrm{CE}}=5.0 \mathrm{Vdc}$ |  |  | 40 | --- |  |
| Base-Emitter Voltage Non-Saturated$\mathrm{V}_{\mathrm{CE}}=5.0 \mathrm{Vdc}, \mathrm{I}_{\mathrm{C}}=2.5 \mathrm{Adc}$ |  | $\mathrm{V}_{\text {BE }}$ |  | 1.45 | Vdc |
|  |  |  |  |  |
| Collector-Emitter Saturation Voltage |  |  | $\mathrm{V}_{\mathrm{CE} \text { (sat) }}$ |  |  |  |
| $\mathrm{I}_{\mathrm{C}}=2.5 \mathrm{Adc}, \mathrm{I}_{\mathrm{B}}=250 \mathrm{mAdc}$ |  |  |  | 0.75 | Vdc |
| $\mathrm{I}_{\mathrm{C}}=5.0 \mathrm{Adc}, \mathrm{I}_{\mathrm{B}}=500 \mathrm{mAdc}$ |  |  |  | 1.5 |  |
| Base-Emitter Saturation Voltage |  | $\mathrm{V}_{\text {BE(sat) }}$ |  |  |  |
| $\mathrm{I}_{\mathrm{C}}=2.5 \mathrm{Adc}, \mathrm{I}_{\mathrm{B}}=250 \mathrm{mAdc}$ |  |  |  | 1.45 | Vdc |
| $\mathrm{I}_{\mathrm{C}}=5.0 \mathrm{Adc}, \mathrm{I}_{\mathrm{B}}=500 \mathrm{mAdc}$ |  |  |  | 2.2 |  |

DYNAMIC CHARACTERISTICS

| Parameters / Test Conditions | Symbol | Min. | Max. | Unit |
| :--- | :---: | :---: | :---: | :---: |
| Magnitude of Common Emitter Small-Signal Short-Circuit. Forward Current |  |  |  |  |
| Transfer Ratio |  |  |  |  |
| $\mathrm{I}_{\mathrm{C}}=500 \mathrm{~mA}, \mathrm{~V}_{\mathrm{CE}}=5.0 \mathrm{Vdc}, \mathrm{f}=10 \mathrm{MHz}$ | 2 N 5002 | $\left\|\mathrm{~h}_{\mathrm{fe}}\right\|$ | 6.0 |  |
| Output Capacitance |  | 7.0 |  |  |
| $\mathrm{~V}_{\mathrm{CB}}=10 \mathrm{Vdc}$ | $\mathrm{C}_{\mathrm{obo}}$ |  | 2504 | pF |

## SWITCHING CHARACTERISTICS

| Parameters / Test Conditions |  | Symbol | Min. | Max. | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: |
| Turn-On Time | $\begin{aligned} & \mathrm{I}_{\mathrm{C}}=5 \mathrm{Adc} ; \mathrm{I}_{\mathrm{B} 1}=500 \mathrm{mAdc} \\ & \mathrm{I}_{\mathrm{B} 2}=-500 \mathrm{mAdc} \\ & \mathrm{~V}_{\mathrm{BE}(\mathrm{OFF})}=3.7 \mathrm{Vdc} \\ & \mathrm{R}_{\mathrm{L}}=6 \Omega \end{aligned}$ | $\mathrm{t}_{\text {on }}$ |  | 0.5 | $\mu \mathrm{s}$ |
| Storage Time |  | $\mathrm{t}_{\text {s }}$ |  | 1.4 | $\mu \mathrm{s}$ |
| Fall Time |  | $\mathrm{t}_{\mathrm{f}}$ |  | 0.5 | $\mu \mathrm{s}$ |
| Turn-Off Time |  | $\mathrm{t}_{\text {off }}$ |  | 1.5 | $\mu \mathrm{s}$ |

## SAFE OPERATING AREA

## DC Tests

$\mathrm{T}_{\mathrm{C}}=+25^{\circ} \mathrm{C}, \mathrm{V}_{\mathrm{CE}}=0, \mathrm{tp}=1 \mathrm{~s}, 1$ Cycle

## Test 1

$\mathrm{V}_{\mathrm{CE}}=12 \mathrm{Vdc}, \mathrm{I}_{\mathrm{C}}=5.0 \mathrm{Adc}$

## Test 2

$\mathrm{V}_{\mathrm{CE}}=32 \mathrm{Vdc}, \mathrm{I}_{\mathrm{C}}=1.7 \mathrm{Adc}$

## Test 3

$\mathrm{V}_{\mathrm{CE}}=80 \mathrm{Vdc}, \mathrm{I}_{\mathrm{C}}=100 \mathrm{mAdc}$

## X-ON Electronics

Largest Supplier of Electrical and Electronic Components
Click to view similar products for Bipolar Transistors - BJT category:
Click to view products by Microsemi manufacturer:
Other Similar products are found below :
619691C MCH4017-TL-H MJ15024/WS MJ15025/WS BC546/116 BC556/FSC BC557/116 BSW67A HN7G01FU-A(T5L,F,T NJVMJD148T4G NSVMMBT6520LT1G NTE187A NTE195A NTE2302 NTE2330 NTE2353 NTE316 IMX9T110 NTE63 NTE65 C4460 SBC846BLT3G 2SA1419T-TD-H 2SA1721-O(TE85L,F) 2SA1727TLP 2SA2126-E 2SB1202T-TL-E 2SB1204S-TL-E 2SC5488A-TL-H 2SD2150T100R SP000011176 FMC5AT148 2N2369ADCSM 2SB1202S-TL-E 2SC2412KT146S 2SC4618TLN 2SC5490A-TL-H 2SD1816S-TL-E 2SD1816T-TL-E CMXT2207 TR CPH6501-TL-E MCH4021-TL-E BC557B TTC012(Q) BULD128DT4 JANTX2N3810 Jantx2N5416 US6T6TR KSF350 068071B

